

### **Amendments to the Drawings**

Correction to the drawings has been made. Specifically, Fig. 8 has been corrected to add the reference numeral 4b for a first limiting structure. A replacement sheet for Fig. 8, which includes Fig. 7 as originally filed, accompanies this response.

With the entry of this response and submission of a replacement drawing for Fig. 8, Applicants kindly request withdrawal of the objection to the drawings.

### **Amendments to the Specification**

Kindly replace the paragraph bridging pages 11-12 with the following paragraph:

The sensors are fabricated using known techniques. See US 5,376,255 and US 5,376,2565 6,440,296 which describe the formation of such structures. The confinement structure may be created by a so-called "backend-process", i.e. after the transducer has been integrated into or created on the silicon wafer. At that stage, the wafer is covered in a passivation layer, such as a layer made from plasma-enhanced chemical vapour deposition (PECVD)-deposited SiN or other passivation layers, such as oxides, oxynitrides or resist layers. The passivation layer is removed in the area around the transducer in order to provide access for the analytes to be measured.

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At page 19, kindly replace the paragraph at lines 20-22 with the following paragraph:

The confinement structures of the present invention may also be included in sensors with have other biosensors and chemical sensors known in the art, such as those described in US 5,376,255 and US 5,376,2565 6,440,296.